

# SKCD 28 C 170 I4F



## CAL-DIODE

$I_F = 40 \text{ A}^1$   
 $V_{RRM} = 1700 \text{ V}$   
 Size:  $5,3 \times 5,3 \text{ mm}^2$

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#### Features

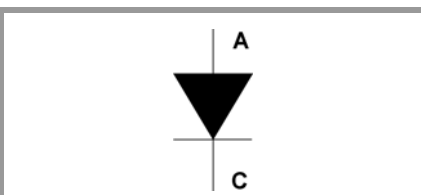
- max. junction temperature  $175 \text{ }^\circ\text{C}$
- low forward voltage drop
- soft reverse recovery behavior
- low switching losses

#### Typical Applications\*

- freewheeling diode for IGBT

#### Footnotes

<sup>1)</sup> Nominal IGBT  $I_F$  rating, verified by design and characterization



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Absolute Maximum Ratings			
Symbol	Conditions	Values	Unit
$V_{RRM}$	$T_j = 25 \text{ }^\circ\text{C}$ , $I_R = 0.06 \text{ mA}$	1700	V
$I_{FSM}$	10 ms	$T_j = 25 \text{ }^\circ\text{C}$	280
	sin 180°	$T_j = 150 \text{ }^\circ\text{C}$	280
$i^2t$	$T_j = 150 \text{ }^\circ\text{C}$ , $t_p = 10 \text{ ms}$ , sin 180°	392	$\text{A}^2\text{s}$
$T_{jmax}$		175	$^\circ\text{C}$

Electrical Characteristics					
Symbol	Conditions	min.	typ.	max.	Unit
$I_{F(AV)}$	$T_c = 80 \text{ }^\circ\text{C}$ , $T_j = 175 \text{ }^\circ\text{C}$ , $F_r = \text{PI}/2$ , Semitrans Assembly; $R_{th(j-c)} = 1.1 \text{ K/W}$		30		A
$I_R$	$T_j = 25 \text{ }^\circ\text{C}$ , $V_{RRM} = 1700 \text{ V}$			0.06	mA
	$T_j = 150 \text{ }^\circ\text{C}$ , $V_{RRM} = 1700 \text{ V}$			11.00	mA
$V_F$	$T_j = 25 \text{ }^\circ\text{C}$ , $I_F = 23 \text{ A}$		1.71	2.03	V
	$T_j = 150 \text{ }^\circ\text{C}$ , $I_F = 23 \text{ A}$		1.69	1.99	V
	$T_j = 175 \text{ }^\circ\text{C}$ , $I_F = 23 \text{ A}$		1.61	1.92	V
$V_{(TO)}$	$T_j = 150 \text{ }^\circ\text{C}$		1.08	1.22	V
$r_T$	$T_j = 150 \text{ }^\circ\text{C}$		26.52	33.48	$\text{m}\Omega$
$V_{(TO)}$	$T_j = 175 \text{ }^\circ\text{C}$		1.01	1.19	V
	$T_j = 175 \text{ }^\circ\text{C}$		26.09	31.74	$\text{m}\Omega$

Dynamic Characteristics					
Symbol	Conditions	min.	typ.	max.	Unit
$E_{rr}$	$T_j = 25 \text{ }^\circ\text{C}$ , 40 A, 1200 V, 800 A/ $\mu\text{s}$		5		mJ
$E_{rr}$	$T_j = 150 \text{ }^\circ\text{C}$ , 40 A, 1200 V, 800 A/ $\mu\text{s}$		12		mJ
$Q_{rr}$	$T_j = 25 \text{ }^\circ\text{C}$ , 40 A, 1200 V, 800 A/ $\mu\text{s}$		8.5		$\mu\text{C}$
$Q_{rr}$	$T_j = 150 \text{ }^\circ\text{C}$ , 40 A, 1200 V, 800 A/ $\mu\text{s}$		18		$\mu\text{C}$
$I_{rrm}$	$T_j = 25 \text{ }^\circ\text{C}$ , 40 A, 1200 V, 800 A/ $\mu\text{s}$		38		A
$I_{rrm}$	$T_j = 150 \text{ }^\circ\text{C}$ , 40 A, 1200 V, 800 A/ $\mu\text{s}$		50		A

Thermal Characteristics					
Symbol	Conditions	min.	typ.	max.	Unit
$T_j$		-40		175	$^\circ\text{C}$
$T_{stg}$		-40		175	$^\circ\text{C}$
$T_{solder}$	10 min.			250	$^\circ\text{C}$
$T_{solder}$	5 min.			320	$^\circ\text{C}$

Mechanical Characteristics			
Symbol	Conditions	Values	Unit
Raster size		5,3 x 5,3	$\text{mm}^2$
Area total		28,09	$\text{mm}^2$
Anode	Metallization	bondable (Al)	
Cathode	Metallization	solderable (Ag/Ni)	
Wire bond		Al, typ. diameter = 300 $\mu\text{m}$	
Package		150 mm wafer frame	
Chips / Package		528	pcs

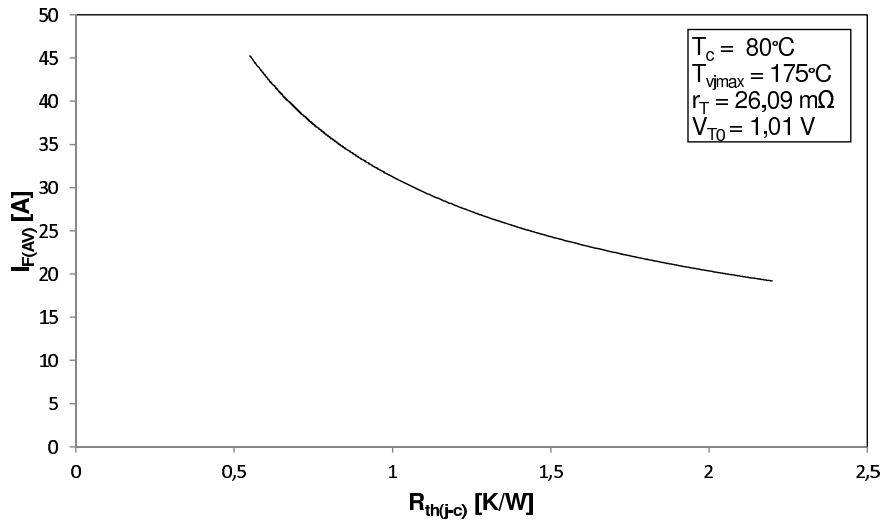
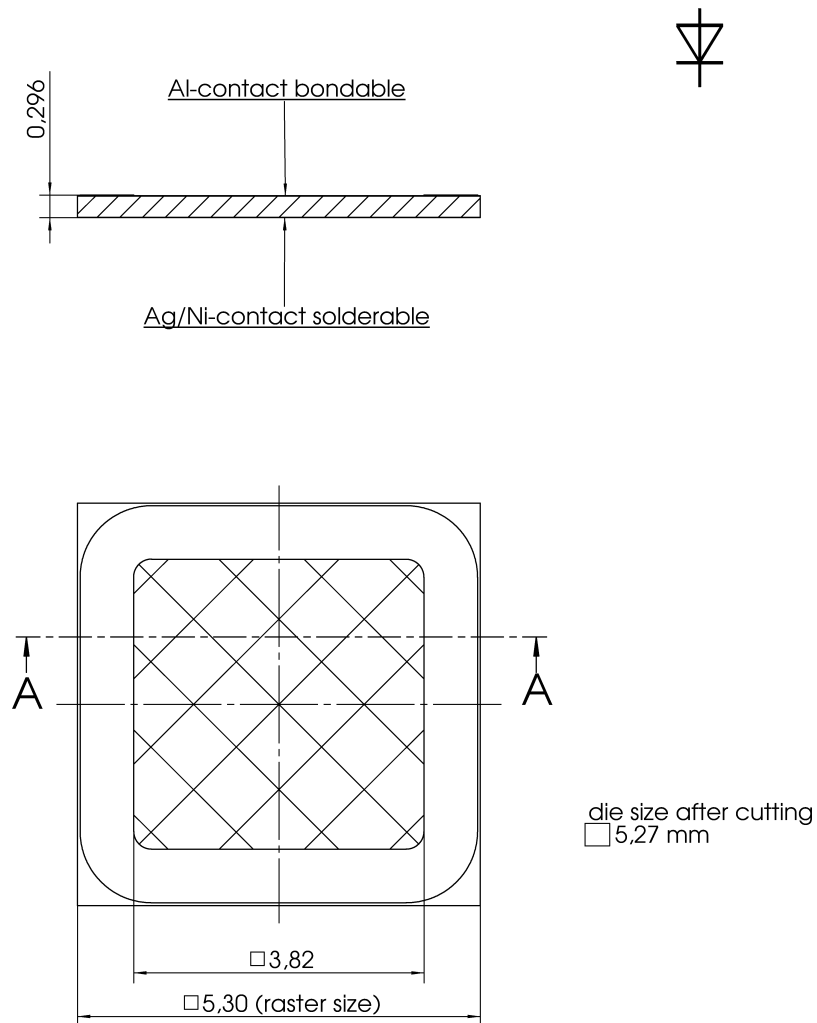


Fig. 1: Rated current vs. thermal resistance



This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX

\* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our staff.